

	Hits	Search Text	DBs
22	8	MEMS and LATENT ADJ MASK\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	1	MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	11	MEMS and LATENT WITH MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	5	MEMS and LATENT SAME MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))) (MEMS and LATENT WITH MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
26	308	MEMS and LATENT AND MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))) (MEMS and LATENT WITH MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3)))) (MEMS and LATENT SAME MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))) (MEMS and LATENT WITH MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
27	131	MEMS SAME LATENT AND MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))) (MEMS and LATENT WITH MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3)))) (MEMS and LATENT SAME MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))) (MEMS and LATENT WITH MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
28	0	MEMS WITH LATENT AND MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))) (MEMS and LATENT WITH MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3)))) (MEMS and LATENT SAME MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))) (MEMS and LATENT WITH MASK\$3 not ((MEMS and LATENT ADJ MASK\$3) (MEMS and LATENT near MASK\$3 not (MEMS and LATENT ADJ MASK\$3))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
29	109	mems AND GATE ADJ OXIDE	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
30	13	mems and (gate adj oxide) with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
31	13	mems and (gate adj oxide) same nitride not (mems and (gate adj oxide) with nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
32	177	lab-on-a-chip "lab-on-a-chip" "lab on a chip"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
33	0	(lab-on-a-chip "lab-on-a-chip" "lab on a chip") and locos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
34	0	(lab-on-a-chip "lab-on-a-chip" "lab on a chip") and smile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
35	2	(lab-on-a-chip "lab-on-a-chip" "lab on a chip") and latent	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
1	8	mems and delayed adj locos	USPAT; US-PGPUB; EPO; JPO; DERWENT;
2	62	mems and locos	USPAT; US-PGPUB; EPO; JPO; DERWENT;
3	54	(mems and locos) not (mems and delayed adj locos)	USPAT; US-PGPUB; EPO; JPO; DERWENT;
4	8	((mems and locos) not (mems and delayed adj locos)) and (si3n4 "Si.sub.3 N.sub.4" nitride) and thermal\$3 adj oxid\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	2	("6464892").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;
6	15	("4764244" "4911783" "5006202" "5131978" "5332469" "5542558" "5628917" "5658471" "5683591" "5690841" "5717251" "5770465" "6020272" "6174820"	USPAT
7	2	("6444138").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;
8	8	("4911783" "5006202" "5131978" "5717251" "5770465" "6020272" "6136243" "6174820").PN.	USPAT
9	7	((("4764244" "4911783" "5006202" "5131978" "5332469" "5542558" "5628917" "5658471" "5683591" "5690841" "5717251" "5770465" "6020272" "6174820" "6136243").PN.) not ((("4911783" "5006202" "5131978" "5717251" "5770465" "6020272" "6136243" "6174820").PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	8	mems and latent adj mask\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT;
11	3999	(MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj	USPAT; US-PGPUB; EPO; JPO; DERWENT;
12	2480	((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side)) and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	1440	((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side)) and etch\$3) and (photoresist resist photomask\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	1126	(((((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side)) and etch\$3) and (photoresist resist photomask\$3)) and (MEMS wafer substrate workpiece silicon) same oxide with (((first and second) both) adj side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	906	(((((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side)) and etch\$3) and (photoresist resist photomask\$3)) and (MEMS wafer substrate workpiece silicon) same oxide with (((first and second) both) adj side)) and (MEMS wafer substrate workpiece silicon) with oxide with (((first and second) both) adj side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	330	(((((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side)) and etch\$3) and (photoresist resist photomask\$3)) and (MEMS wafer substrate workpiece silicon) same oxide with (((first and second) both) adj side)) and (MEMS wafer substrate workpiece silicon) with oxide with (((first and second) both) adj side)) and (MEMS wafer substrate workpiece silicon) near oxide with (((first and second) both) adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
17	17	(((((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side)) and etch\$3) and (photoresist resist photomask\$3)) and (MEMS wafer substrate workpiece silicon) same oxide with (((first and second) both) adj side)) and (MEMS wafer substrate workpiece silicon) with oxide with (((first and second) both) adj side)) and (MEMS wafer substrate workpiece silicon) near oxide with (((first and second) both) adj side)) and (MEMS wafer substrate workpiece silicon) near oxide near (((first and second) both) adj side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	18	SMILE and MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT;
19	9	((multilevel multi-level) near etch\$3) and MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT;
20	15	("4764244" "4911783" "5006202" "5131978" "5332469" "5542558" "5628917" "5658471" "5683591" "5690841" "5717251" "5770465" "6020272" "6174820"	USPAT
21	0	((("4764244" "4911783" "5006202" "5131978" "5332469" "5542558" "5628917" "5658471" "5683591" "5690841" "5717251" "5770465" "6020272" "6174820" "6136243").PN.) and locos	USPAT
22	1	((("4764244" "4911783" "5006202" "5131978" "5332469" "5542558" "5628917" "5658471" "5683591" "5690841" "5717251" "5770465" "6020272" "6174820" "6136243").PN.) and latent	USPAT
23	0	((("4764244" "4911783" "5006202" "5131978" "5332469" "5542558" "5628917" "5658471" "5683591" "5690841" "5717251" "5770465" "6020272" "6174820" "6136243").PN.) and smile	USPAT
24	52	MEMS and (smile locos latent adj mask\$3)	USPAT
25	9	MEMS and smile	USPAT
26	2	MEMS and delayed adj locos	USPAT
27	45	MEMS and locos	USPAT
28	2	MEMS and latent adj mask\$3	USPAT

	Hits	Search Text	DBs
1	8	mems and delayed adj locos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	62	mems and locos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	54	(mems and locos) not (mems and delayed adj locos)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	8	((mems and locos) not (mems and delayed adj locos)) and (si3n4 "si.sub.3 N.sub.4" nitride) and thermal\$3 adj oxid\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	2	("6464892").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	15	("4764244" "4911783" "5006202" "5131978" "5332469" "5542558" "5628917" "5658471" "5683591" "5690841" "5717251" "5770465" "6020272" "6174820"	USPAT
7	2	("6444138").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	8	("4911783" "5006202" "5131978" "5717251" "5770465" "6020272" "6136243" "6174820").PN.	USPAT
9	7	((("4764244" "4911783" "5006202" "5131978" "5332469" "5542558" "5628917" "5658471" "5683591" "5690841" "5717251" "5770465" "6020272" "6174820" "6136243").PN.) not ((("4911783" "5006202" "5131978" "5717251" "5770465" "6020272" "6136243" "6174820").PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	11	MEMS and (dope dopant doping) and ((pad adj oxide) with (nitride SiN Si3N4 "si.sub.3 N.sub.4")) and contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	1310	(dope dopant doping) and ((pad adj oxide) with (nitride SiN Si3N4 "si.sub.3 N.sub.4")) and contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	225	((dope dopant doping) and ((pad adj oxide) with (nitride SiN Si3N4 "si.sub.3 N.sub.4")) and contact) and deposit\$3 near metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	1	((dope dopant doping) and ((pad adj oxide) with (nitride SiN Si3N4 "si.sub.3 N.sub.4")) and contact) and deposit\$3 near metal) and (dope dopant doping) with "same" near (substrate wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	13	((dope dopant doping) and ((pad adj oxide) with (nitride SiN Si3N4 "si.sub.3 N.sub.4")) and contact) and (dope dopant doping) with "same" near (substrate wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	1452	(dope dopant doping) and ((pad adj oxide) same (nitride SiN Si3N4 "si.sub.3 N.sub.4")) and contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	1621	(dope dopant doping) and ((pad adj oxide) and (nitride SiN Si3N4 "si.sub.3 N.sub.4")) and contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	15	MEMS and ((dope dopant doping) and ((pad adj oxide) and (nitride SiN Si3N4 "si.sub.3 N.sub.4")) and contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	4	(MEMS and ((dope dopant doping) and ((pad adj oxide) and (nitride SiN Si3N4 "si.sub.3 N.sub.4")) and contact) not (MEMS and (dope dopant doping) and ((pad adj oxide) with (nitride SiN Si3N4 "si.sub.3 N.sub.4")) and contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	72	MEMS and LOCOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	18	MEMS and SMILE	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	1016	MEMS and LATENT	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB